СО	NFIDENTIA	L	MITS	SUBI	SHI I	ELEC	TRIC	C	COF	۲PC	)R/	ATIO	ON					
		PREPARED BY:																
SPECIFICATION		CHECKED BY:					R E						╎╎					
		APPROVED BY:					V	╞					┥┝					
		DATE:														-64		
1. Typ	De	2											Y					
2. Application Light Source				ource														
3. Structure Red Lase				ser Di	Diode													
4. Outline G88036				67														
5. Ab	solute maxim	um ratin	igs															
No.	PARAMETER				SYME	BOL	CONDITION							RATINGS				
(1)	Operation Current				Іор		CW							Fig.1				
(2)	Reverse Voltage				Vrl		-							2				
(3)	Anode-Case Voltage (*1)				Vac		-								-30~30			
(4)	Operating Case Temperature				Tc		-							0~+55				
(5)	Storage Temperature				Tstg		-							-40~+85			°C	
(6) Soldering Temperature					Tso	bl	Lead Length≥ 2mm							320°C, 2sec				
*1: ˈ 6. C	Semiconducto Voltage betwe haracteristics	or Qualit en Φ9 p table	y Assurar backage a	nce Se nd and	ection. ode lead	pin												
						CONDITION				LIMITS								
No.	PAR	AMETEF	METER		MBOL		(Tc=25°C(*2) unless otherwise specified)						MIN.	M	AX.	UINT		
(1)	Output Power					CW, Iop=2.25A, Tc=25°C					2.1		-	w				
				F	ор	CW, Iop=2.95A, Tc=45°C							2.1		-	w		
						CW, Ic	/, Iop=2.50A, Tc=55℃							1.3		-	w	
(2)	Threshold Cu	ld Current			lth	CW, T	Tc=25°C							550			mA	
(3)	Operating Vo	oltage			/op	CW, Iop=2.25A, Tc=25°C							2.25			V		
(4)	Slope Efficie	ncy		η		CW, Tc=25°C								1.2			W/A	
(5)	Peak Wavele	ngth			λр	CW, Ic	W, Iop=2.25A, Tc=25°C							635 639 644			nm	
(6)	Beam Divergence			θ //		CW, Iop=2.25A, Tc=25°C								9			•	
	(Full Width at		θ		CW, Ic	op=2.25	25A, Tc=25°C							65	1		•	
*2: /	Actual measur match an activ	ement to ve layer c=25°C	emperatur temperatı	re is a ure to	djusted that of	in orde stable	er to				_							

These specifications are based on MITSUBISHI's method.

